Electronic supplementary information

Element	Atom%	Std.Dev. ProcCalc.	Line	Int.(cps/uA)	Thickness/nm				
IM-Pt ₂ Si-MS									
Pt	63.359	(0.299) Quan-FP	PtLa	5.0963	74				
Si	36.641	(1.883) Quan-FP	SiKa	0.0230					
IM-Pt ₂ Si-MS (after CV 1000 cycles in H ₂ SO ₄)									
Pt	64.270	(0.299) Quan-FP	PtLa	5.1267	73				
Si	35.730	(1.917) Quan-FP	SiKa	0.0223					

Table S1[†] The composition of IM-Pt₂Si-MS electrode before and after CV



Fig. S1[†] Cyclic voltammograms with different potential ranges of IM-Pt₂Si-MS electrode in 0.5 mol·L⁻¹ H₂SO₄ solution at a sweeping rate of 100 mV·s⁻¹



Fig. S2[†] Linear sweep voltammetry curves of IM-Pt₂Si-MS, Pt-MS and Pt-disk electrodes in 1.0 mol·L⁻¹ KOH solution at a sweeping rate of 5 mV·s⁻¹ in electrochemical active surface areas (ESA).



Fig. S3[†] The fine XPS spectrum analysis of Si in IM-Pt₂Si-MS electrode

Table S2[†] The surface composition of IM-Pt₂Si-MS electrode before and after CV

Nama	Atomic %		
Iname	Pt	Si	
IM-Pt ₂ Si-MS	37.81	62.19	
IM-Pt ₂ Si-MS (after CV 1000 cycles in $H_2SO_{4)}$	37.96	62.04	



Fig. S4[†] Open circuit potentials of IM-Pt₂Si-MS and Pt-MS electrodes in 0.5 mol·L⁻¹

 H_2SO_4 solution.



Fig. S5^{\dagger} The equivalent circuit of the impedance of IM-Pt₂Si-MS and Pt-MS

electrodes

Table S3[†] Impedance parameters of IM-Pt₂Si-MS and Pt-MS electrodes obtained by fitting the experimental data to $R_s(R_fQ_f)(R_{ct}Q_{dl})$ equivalent circuit

Electrocatalyst	R_s	R_{f}	C_{f}	n _f	R _{ct}	C_{dl}	n _{dl}
	$/\Omega \cdot cm^2$	$/\Omega \cdot cm^2$	$/\mu F{\cdot}cm^{-2}$		$/\Omega \cdot cm^2$	$/\mu F{\cdot}cm^{-2}$	
IM-Pt ₂ Si-MS	0.9089	0.5848	2.56	0.96301	1.454	54.8	0.81479
Pt-MS	0.9087	0.5584	2.87	0.87169	3.215	45.4	0.84617



Fig. S6[†] The long-term cyclic voltammograms stability test for IM-Pt₂Si-MS electrode in 0.5 mol·L⁻¹ H₂SO₄ solution at a sweeping rate of 100 mV·s⁻¹.



Fig. S7[†] A plot of sputtering power and deposition rate of Pt (a) and Si (b).